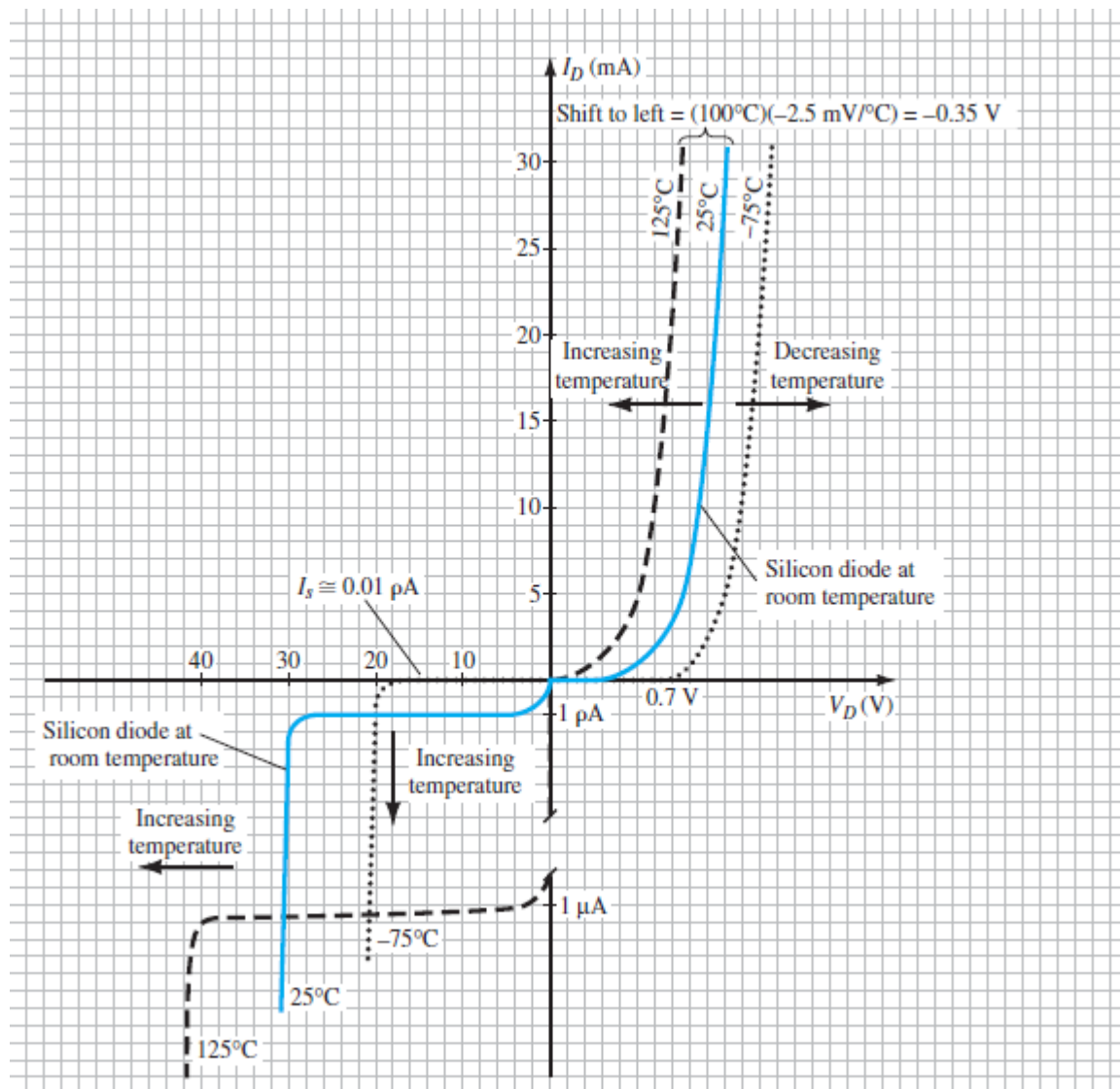


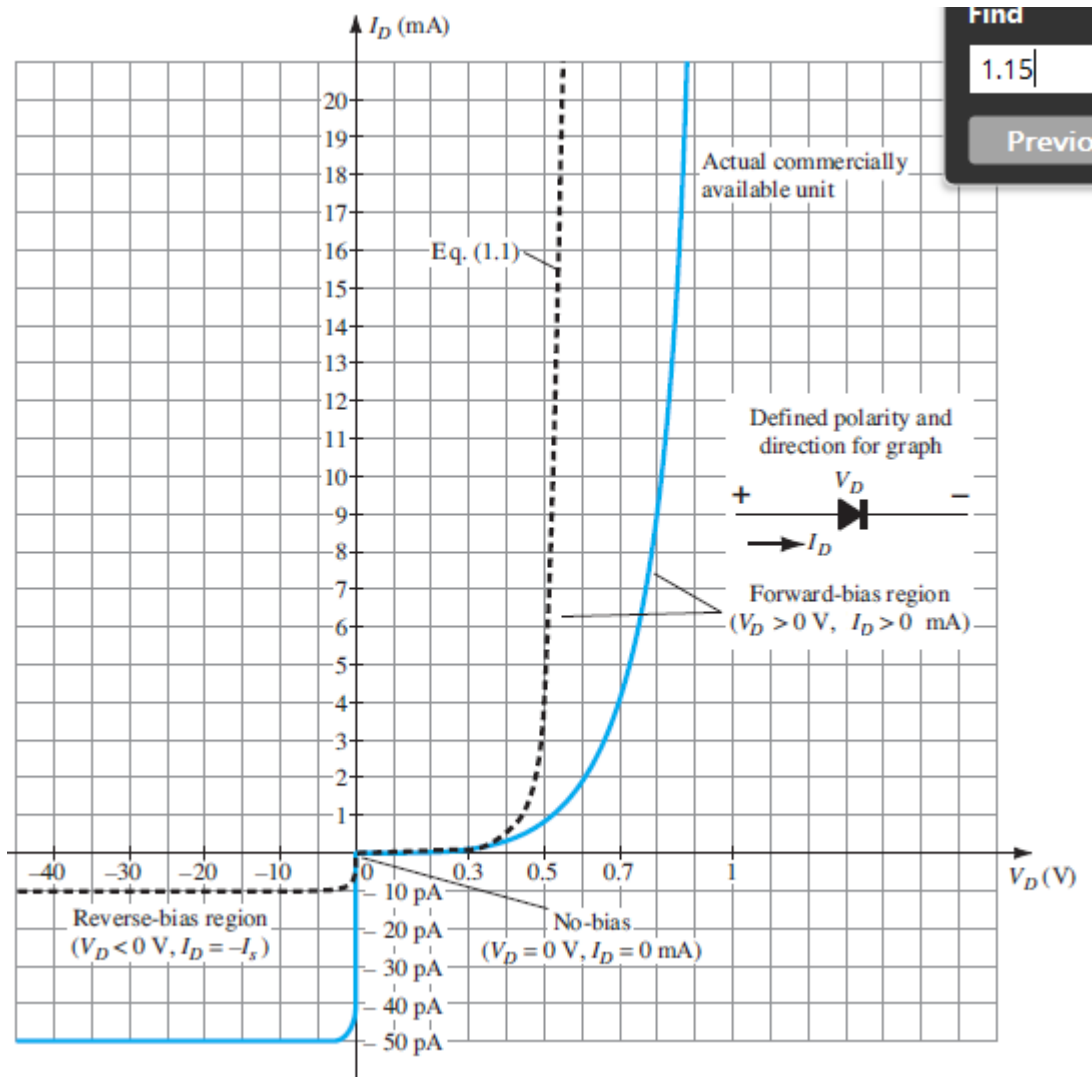
Tutorial 1

Chapter 1 Semiconductors and Diodes

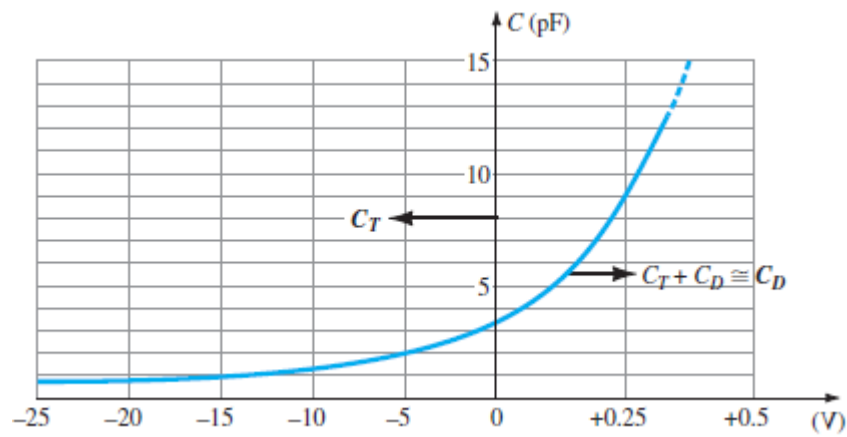
1.
 - a. Determine the thermal voltage for a diode at a temperature of 20°C.
 - b. For the same diode of part (a), find the diode current using Eq. 1.2 if $I_s = 40$ nA, $n = 2$ (low value of V_D), and the applied bias voltage is 0.5 V.
 - c. Repeat for $T = 100^\circ\text{C}$ (boiling point of water). Assume that I_s has increased to 5.0 mA.
2. Given a diode current of 6 mA, $V_T = 26$ mV, $n = 1$, and $I_s = 1$ nA, find the applied voltage V_D .
3. Determine the forward voltage drop across the diode whose characteristics appear below at temperatures of -75°C , 25°C , 125°C and a current of 10 mA. For each temperature, determine the level of saturation current. Compare the extremes of each and comment on the ratio of the two.



4.
 - a. Determine the static or dc resistance of the commercially available diode characteristics shown below at a forward current of 4 mA.
 - b. Repeat at a forward current of 15 mA and compare results.
 - c. Determine the static or dc resistance of the commercially available diode at a reverse voltage of -10 V. How does it compare to the value determined at a reverse voltage of -30 V?

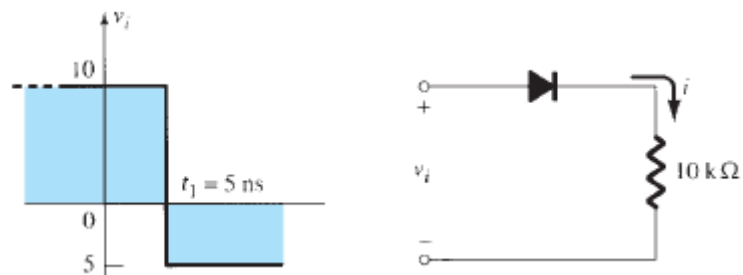


5. a. Determine the dynamic (ac) resistance of the commercially available diode shown above, at a forward current of 10 mA using Eq. (1.5).
 - b. Determine the dynamic (ac) resistance of the diode shown above, at a forward current of 10 mA using Eq. (1.6).
 - c. Compare solutions of parts (a) and (b).
6. a. Referring to capacitance characteristics shown below, determine the transition capacitance at reverse-bias potentials of -25 V and -10 V. What is the ratio of the change in capacitance to the change in voltage?
 - b. Repeat part (a) for reverse-bias potentials of -10 V and -1 V. Determine the ratio of the change in capacitance to the change in voltage.
 - c. How do the ratios determined in parts (a) and (b) compare? What does this tell you about which range may have more areas of practical application?

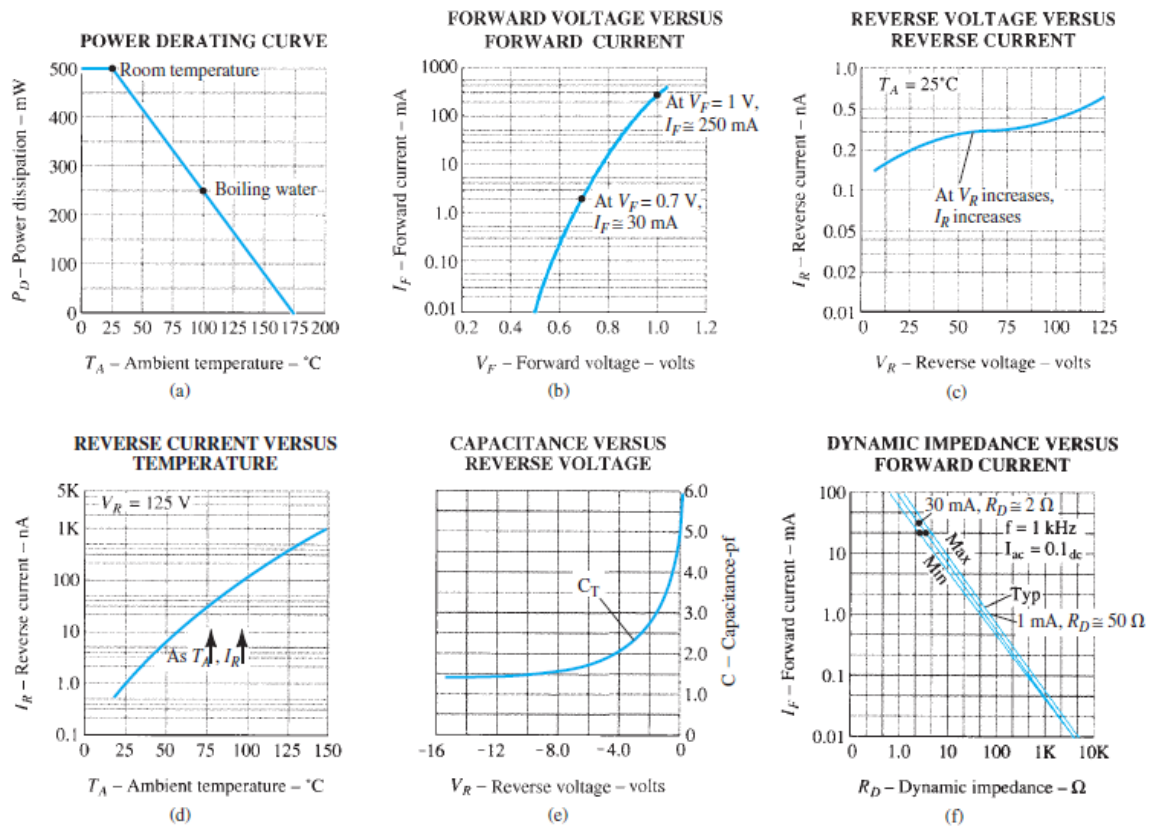


7. The no-bias transition capacitance of a silicon diode is 8 pF with $V_K = 0.7$ V and $n = 1.2$. What is the transition capacitance if the applied reverse bias potential is 5 V?

8. Sketch the waveform for i of the network shown below if $t_r = 2$ ns and the total reverse recovery time is 9 ns.



9. Using the characteristics shown below, determine the maximum power dissipation levels for the diode at room temperature (25°C) and 100°C. Assuming that V_F remains fixed at 0.7 V, how has the maximum level of I_F changed between the two temperature levels?



10. Determine the dynamic impedance for the 24-V diode at $I_Z = 10$ mA for the diode characteristics below. Note that it is a log scale.

